

User's Guide to BGT24LTR11N16

24GHz Radar

About this document

Scope and purpose

This application note is intended to put flesh on the bones of BGT24LTR11N16's datasheet.

The datasheet gives technical data and limits of the device itself but it is not explaining the device in greater detail. This application note takes care of this issue.

The reader will find here:

- Discussion of all different building blocks
- How to operate the different blocks
- Additional measurement data showing behavior over temperature

Intended audience

Hardware engineers and software engineers working on designs with Infineon's BGT24LTR11N16.

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1 Introduction to BGT24LTR11

BGT24LTR11 is Silicon Germanium radar MMIC for signal generation and reception, operating in the 24.0 GHz to 24.25 GHz ISM band. It is based on a 24 GHz fundamental voltage controlled oscillator (VCO). The device was designed with Doppler-radar applications in mind—as it is capable of keeping the transmit signal inside the ISM band without any external PLL — and may also be used in other types of radar such as FMCW or FSK.

A built-in voltage source delivers a VCO tuning voltage which is proportional to absolute temperature (PTAT). When connected to the VCO tuning pin it compensates for the inherent frequency drift of the VCO over temperature thus stabilizing the VCO within the ISM band eliminating the need for a PLL/Microcontroller. An integrated 1:16 frequency divider also allows for external phase lock loop VCO frequency stabilization.

The receiver section uses a low noise amplifier (LNA) in front of a quadrature homodyne down-conversion mixer in order to provide excellent receiver sensitivity. Derived from the internal VCO signal, a RC-polyphase filter (PPF) generates quadrature LO signals for the quadrature mixer. I/Q IF outputs are available through single-ended terminals.

The device is manufactured in a 0.18 μm SiGe:C technology offering a cutoff frequency of 200 GHz. It is packaged in a 16-pin leadless RoHS compliant TSNP package.

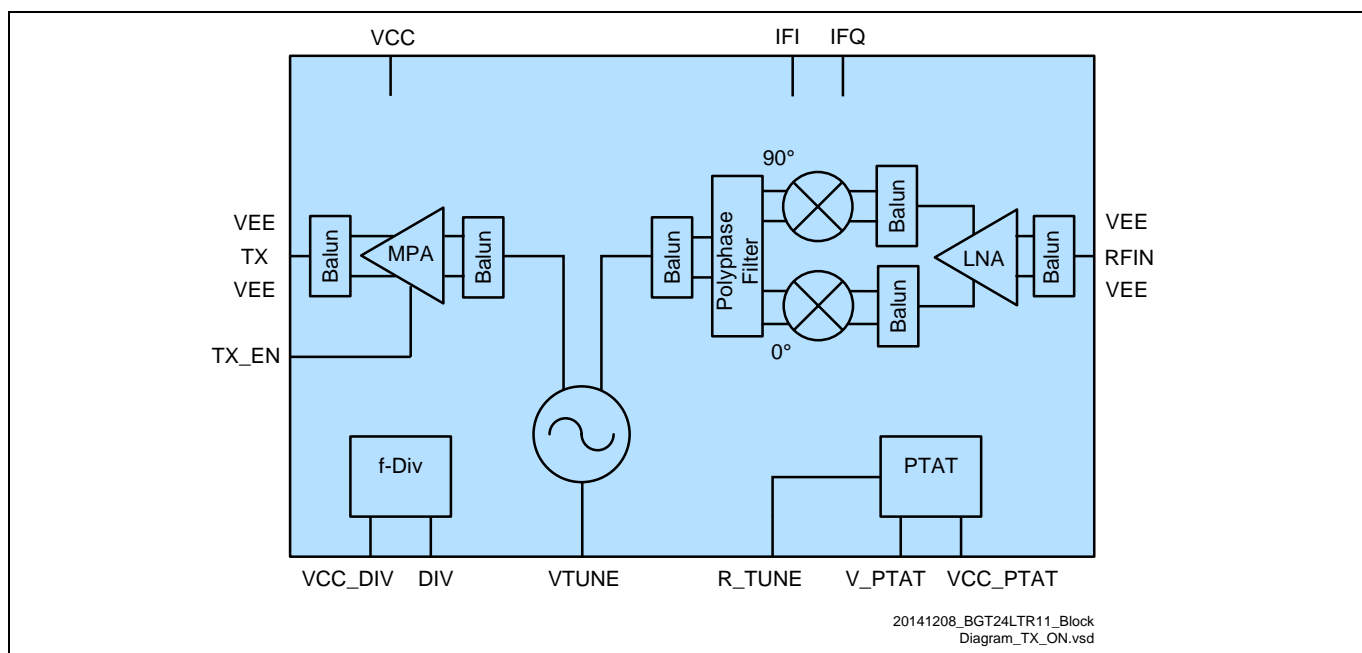


Figure 1 BGT24LTR11N16 Block Diagram

2 Building Blocks

2.1 Transmitter

BGT24LTR11N16 has a single-ended transmitter output TX (pin 11) with a typical output power of 6 dBm. The transmitter's output may be enabled and disabled by applying appropriate voltages to TX_ON (pin 5) as shown in the table below.

Disabling the TX output will not save power as the output will be switched to an internal load while the rest of the chip is still running. This is necessary in case one wants to implement a software controlled oscillator (see section 4.3).

Table 1 Enabling/disabling TX output

Enable TX	Disable TX
Voltage at TX_ON > 2 V	Voltage at TX_ON < 0.8 V

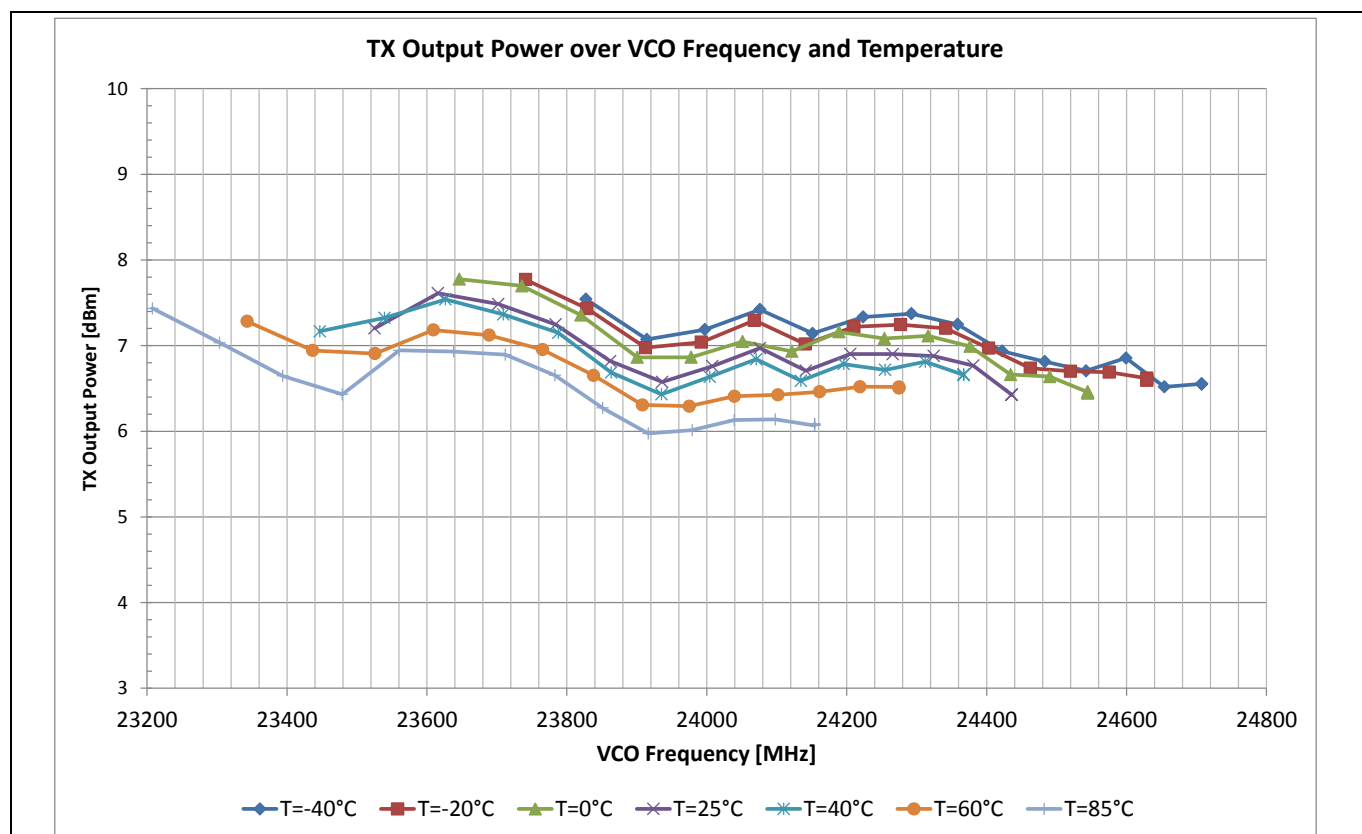


Figure 2 TX output power vs. frequency and temperature

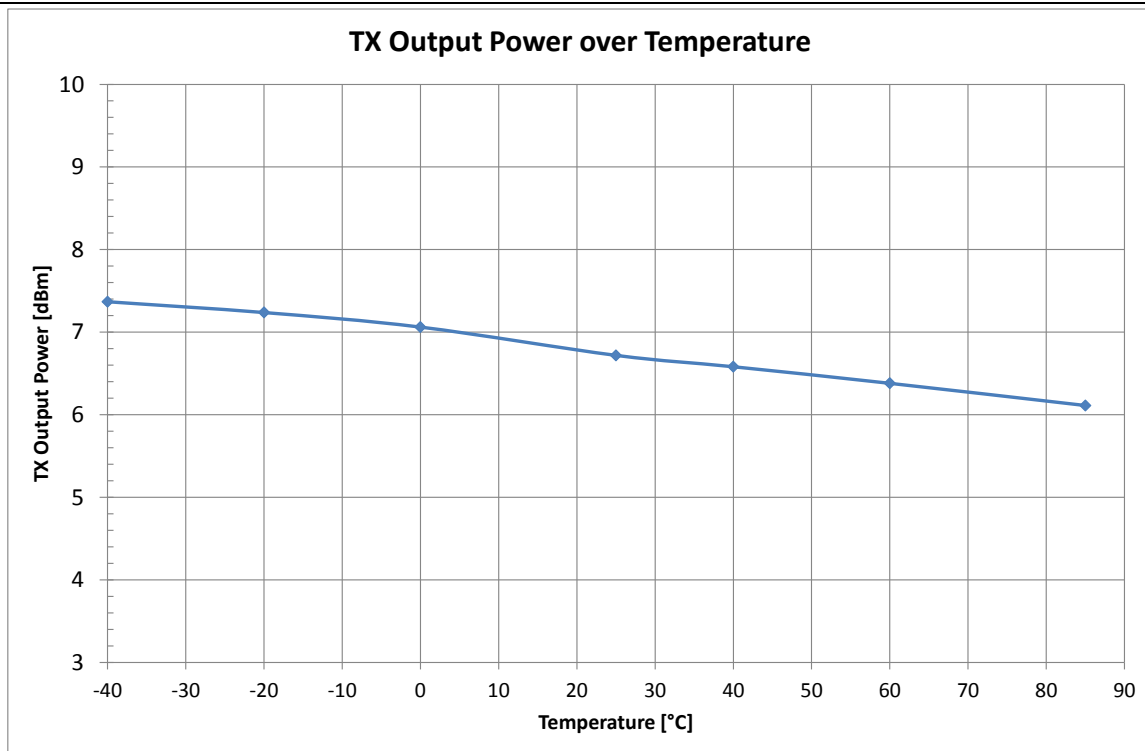


Figure 3 TX output power with VTUNE connected to V_PTAT

2.2 Receiver

The receiver consists of an LNA followed by quadrature direct-conversion mixer. Its input (RX, pin 3) is single-ended. The voltage conversion gain is typically 20 dB with a single side-band noise figure of 10 dB.

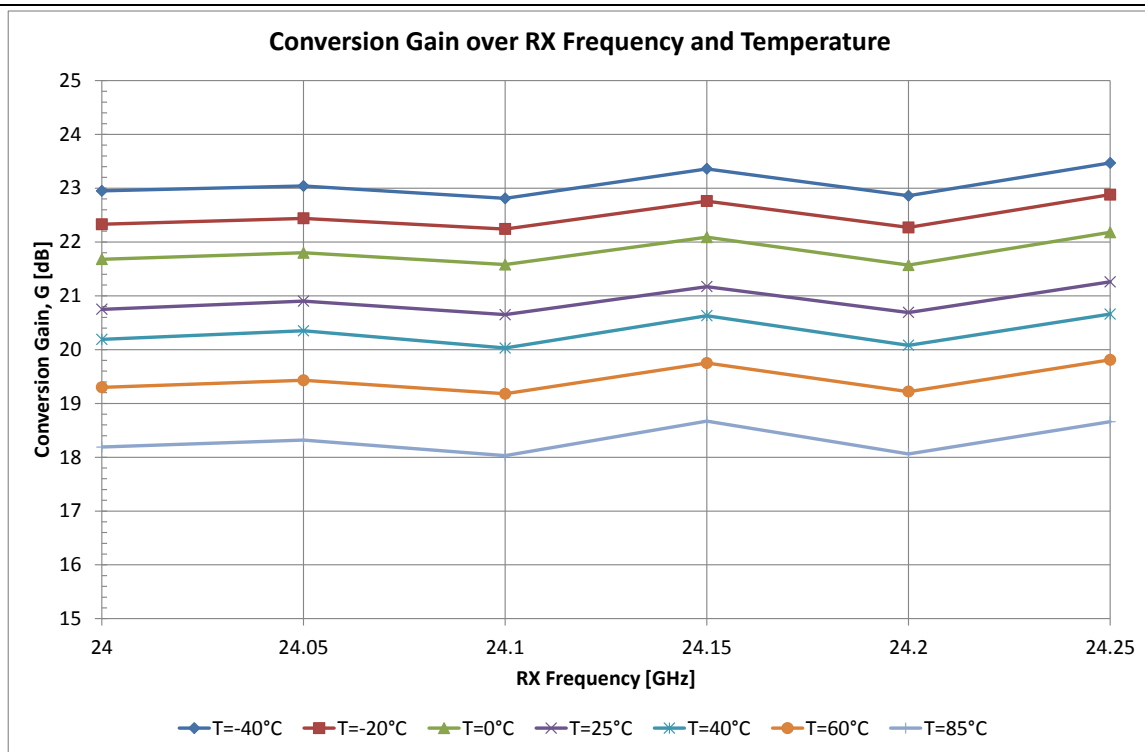


Figure 4 Gain vs. frequency

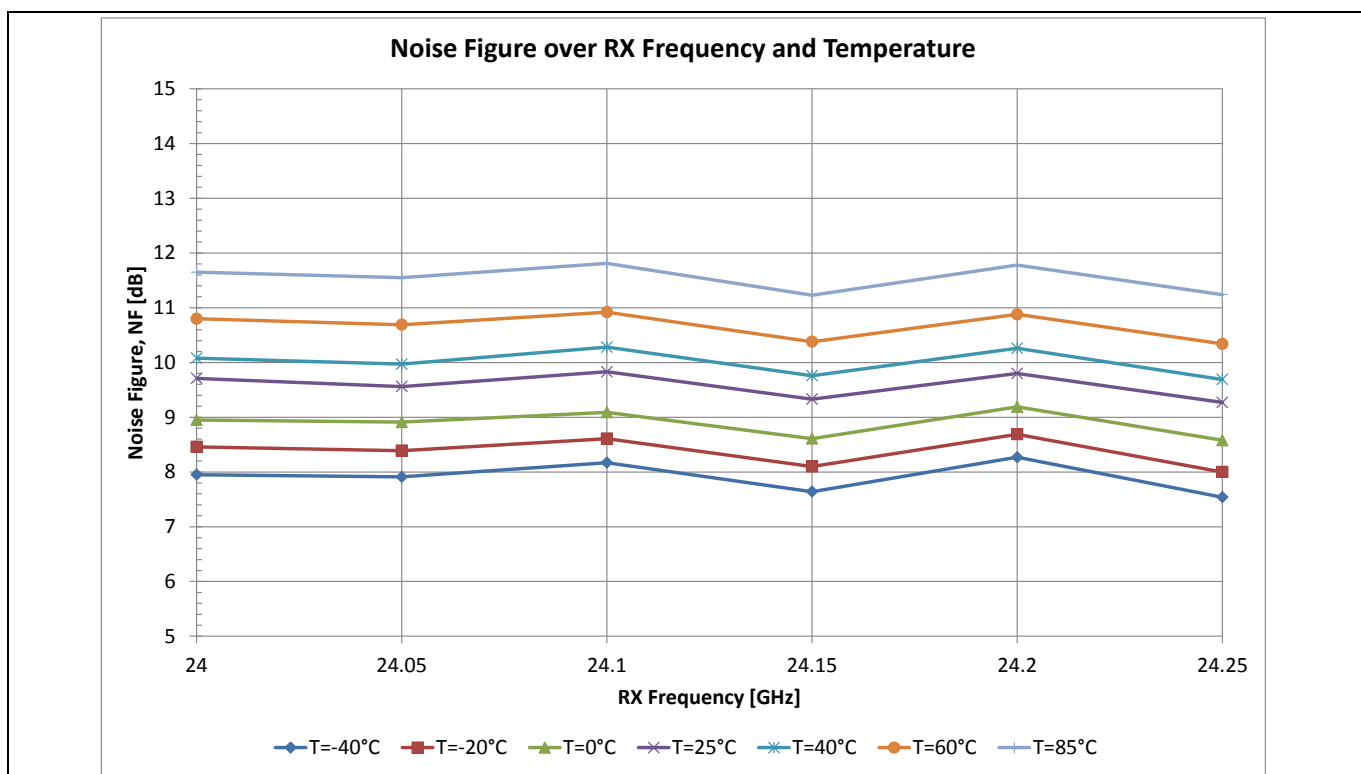


Figure 5 Noise figure vs. frequency

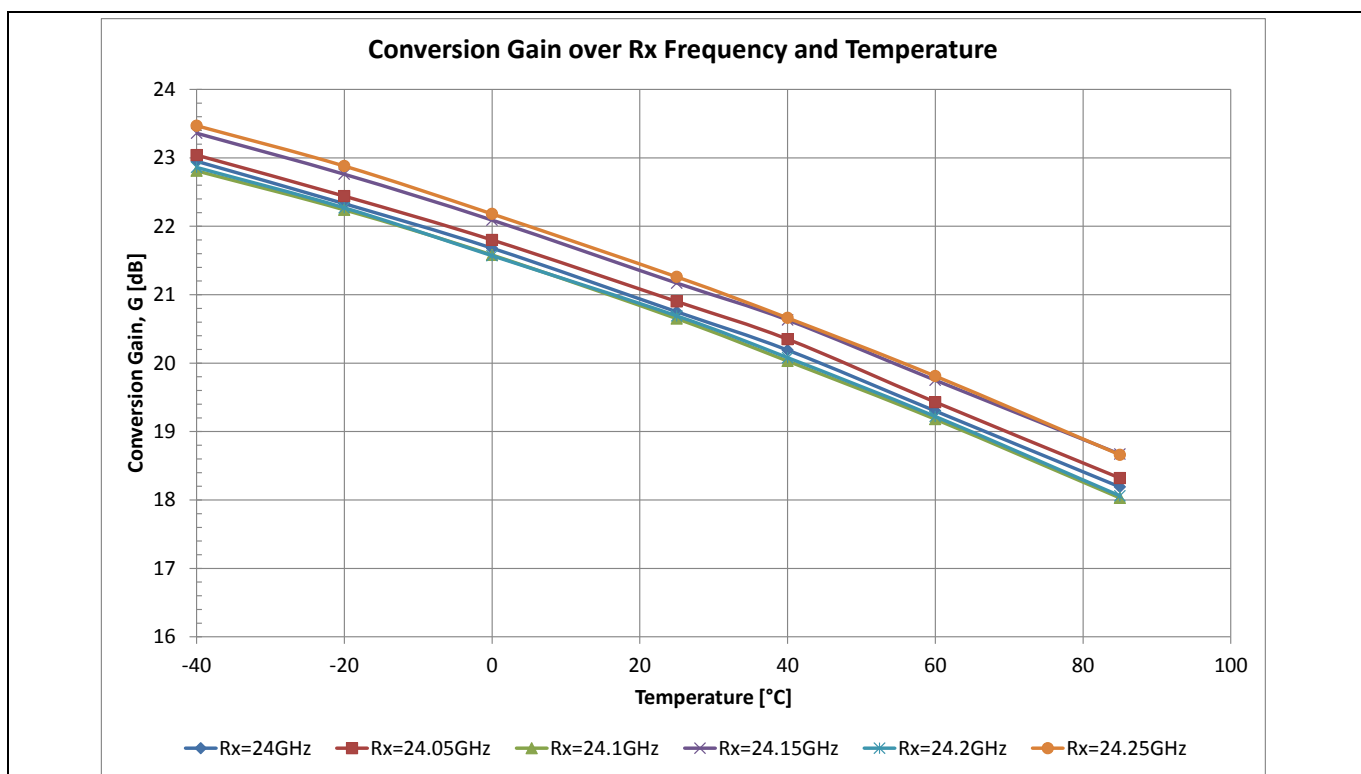


Figure 6 Conversion gain vs. temperature

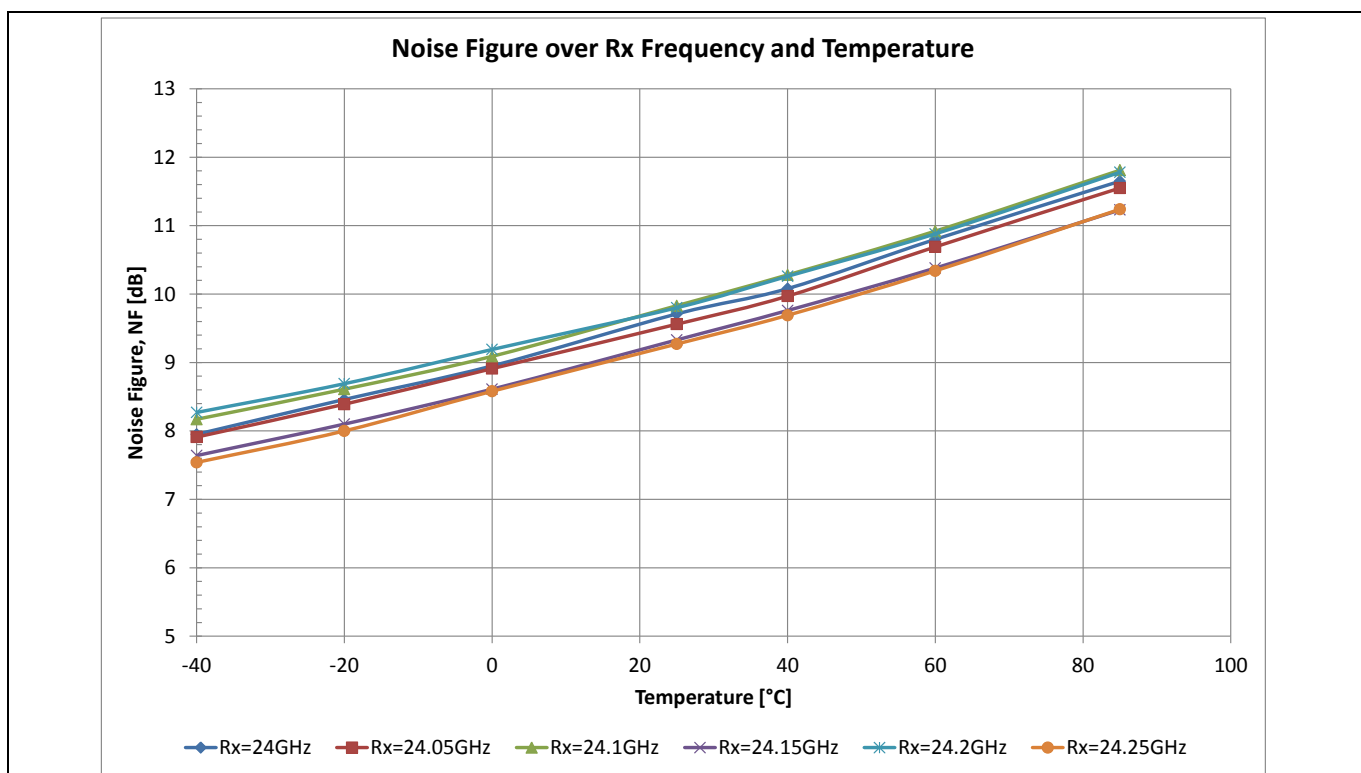


Figure 7 Noise figure vs. temperature

2.3 Voltage Controlled Oscillator (VCO)

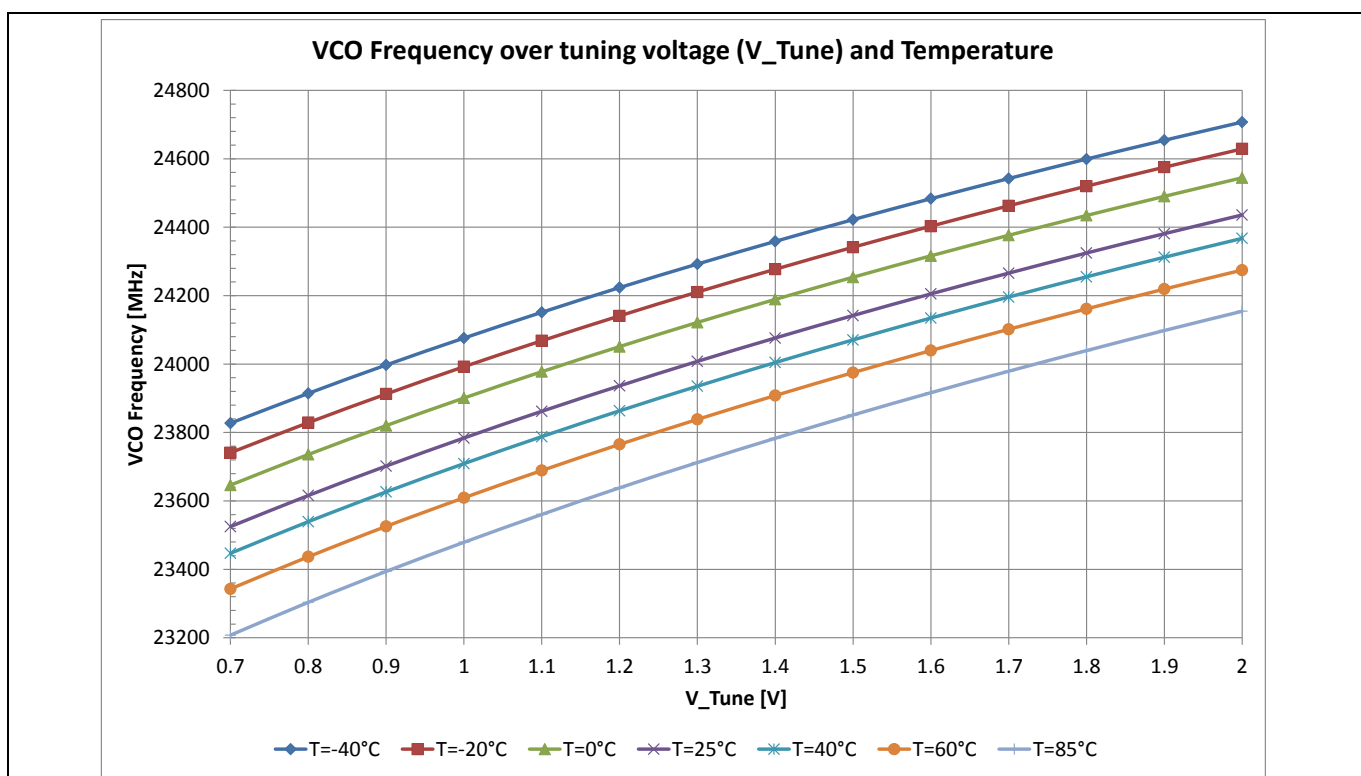


Figure 8 VCO frequency over tuning voltage and temperature

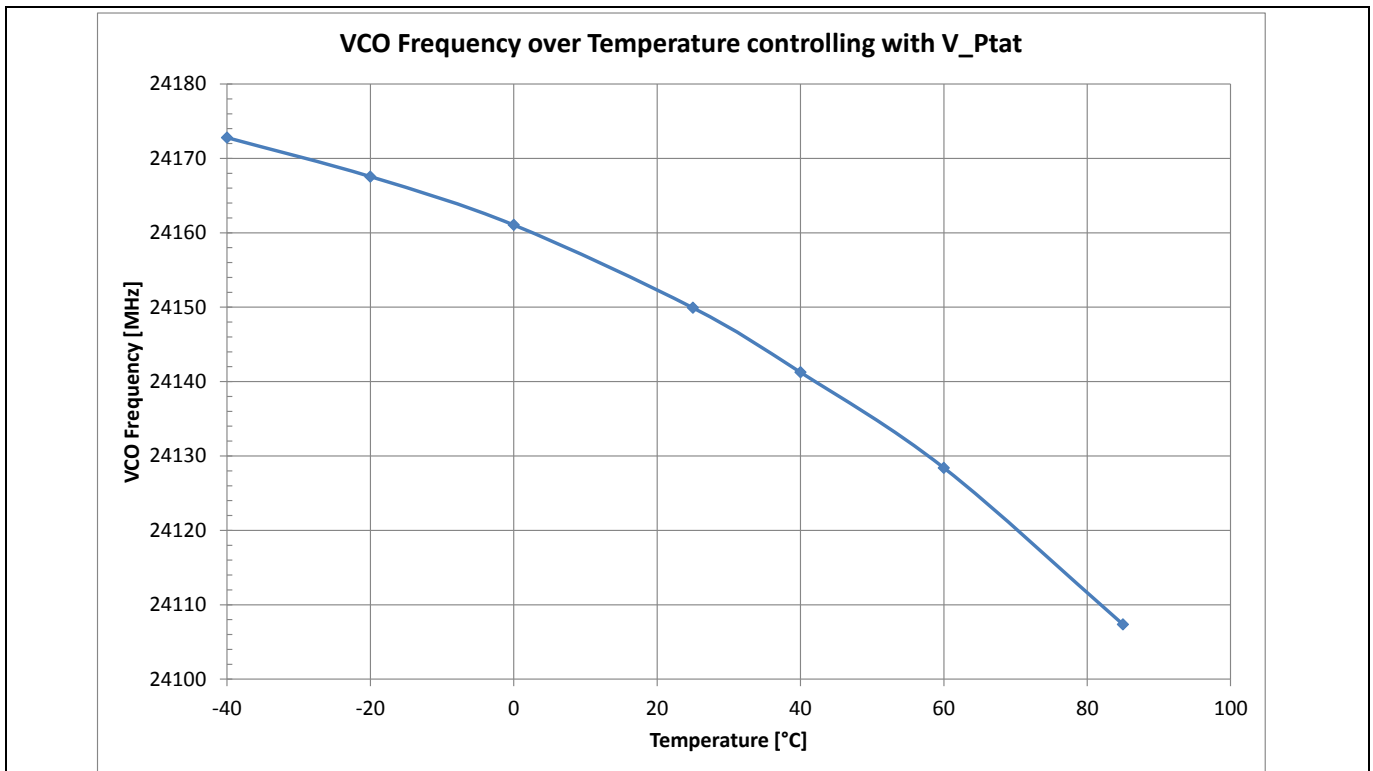


Figure 9 VCO frequency over temperature, VCO controlled by PTAT voltage source

2.4 Proportional to Absolute Temperature (PTAT) Voltage Source

The PTAT voltage source generates a voltage V_{PTAT} at the V_PTAT pin (pin 15) which is proportional to the chip temperature. It is powered separate from VCC via the VCC_PTAT pin (pin 16).

The PTAT voltage source serves two purposes:

- Generating tuning voltage for the VCO in Doppler mode. See section 4.1.
- Temperature sensor measuring chip temperature.

The chip temperature T_{chip} can be calculated from V_{PTAT} using the following equation:

$$T_{chip} / ^\circ\text{C} = 158.7 * (V_{PTAT} / \text{V}) - 217.0 \text{ with } VCC_PTAT = VCC = 3.3 \text{ V and } VCC_DIV \text{ open.}$$

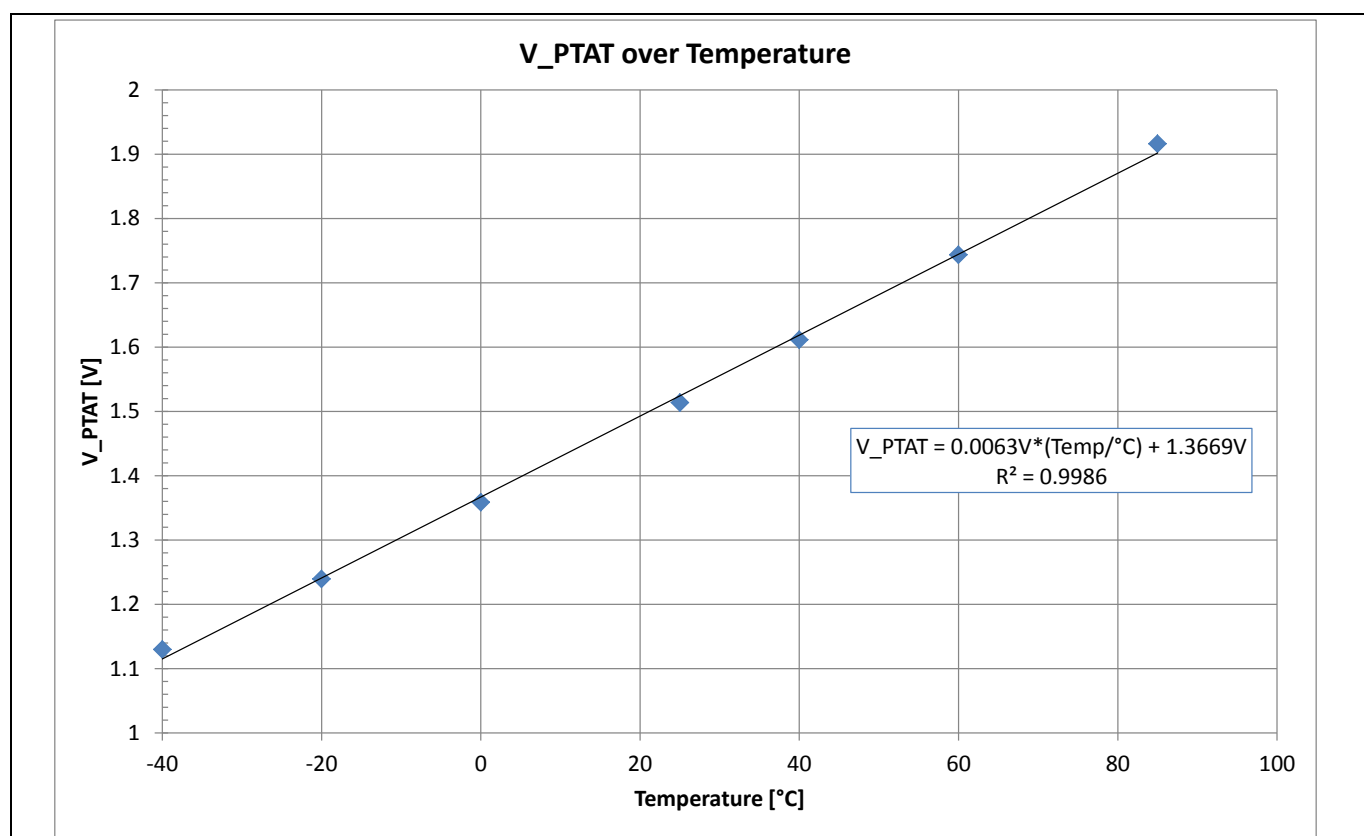


Figure 10 Voltage generated by PTAT voltage source vs. temperature

2.5 Frequency Divider

BGT24LTR11N16's frequency divider has two divider ratios, divide by 16 and divide by 8182 which result in output frequencies of 1.5 GHz and 3 MHz respectively.

Table 2 Setting the divider ratio

Divider ratio	Voltage at VCC_PTAT (pin 16)
16	< 0.8 V
8192	3.3 V

Setting the divider to a 3 MHz output will cause the PTAT to consume current. This ratio is usually used only in case of a software controlled VCO and for this use cases a temperature sensor is required anyways to check the validity of the used look-up table.

3 Evaluation Board

3.1 Schematic Diagram

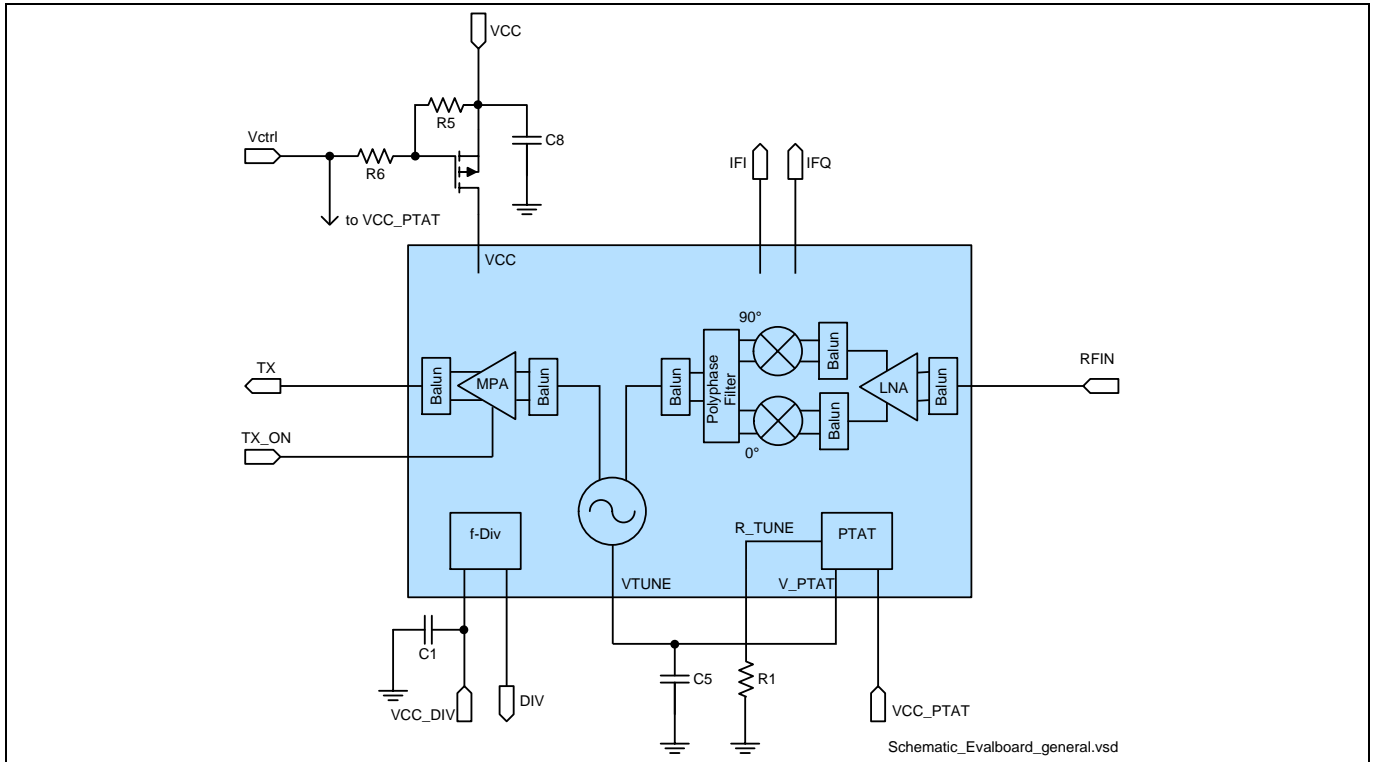


Figure 11 Schematic diagram

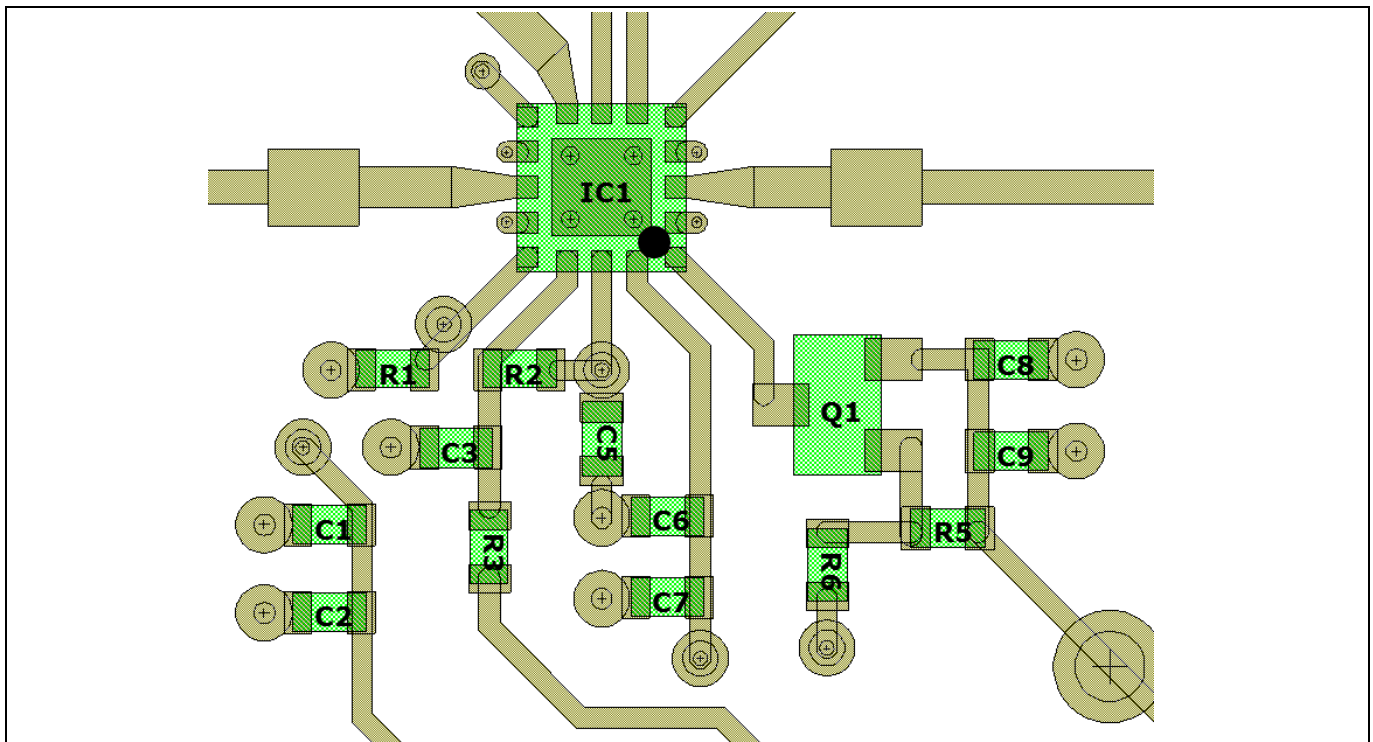


Figure 12 Component placement

Table 3 Bill of materials

Designation	Part type	Value	Package	Manufacturer
C1, C5, C8	Chip capacitor	1 μ F	0402	Various
C2, C3, C6, C7, C9		DNP	0402	
R1	Chip resistor	16 k Ω	0402	Various
R2,R3	Chip resistor	0 Ω	0402	Various
R5	Chip resistor	100 k Ω	0402	Various
R6	Chip resistor	1 k Ω	0402	Various
Q1	p-MOSFET	BSS209PW	SOT-323	Infineon
IC1	Radar MMIC	BGT24LTR11N16	TSNP-16-9	Infineon

3.1.1 Matching Structures

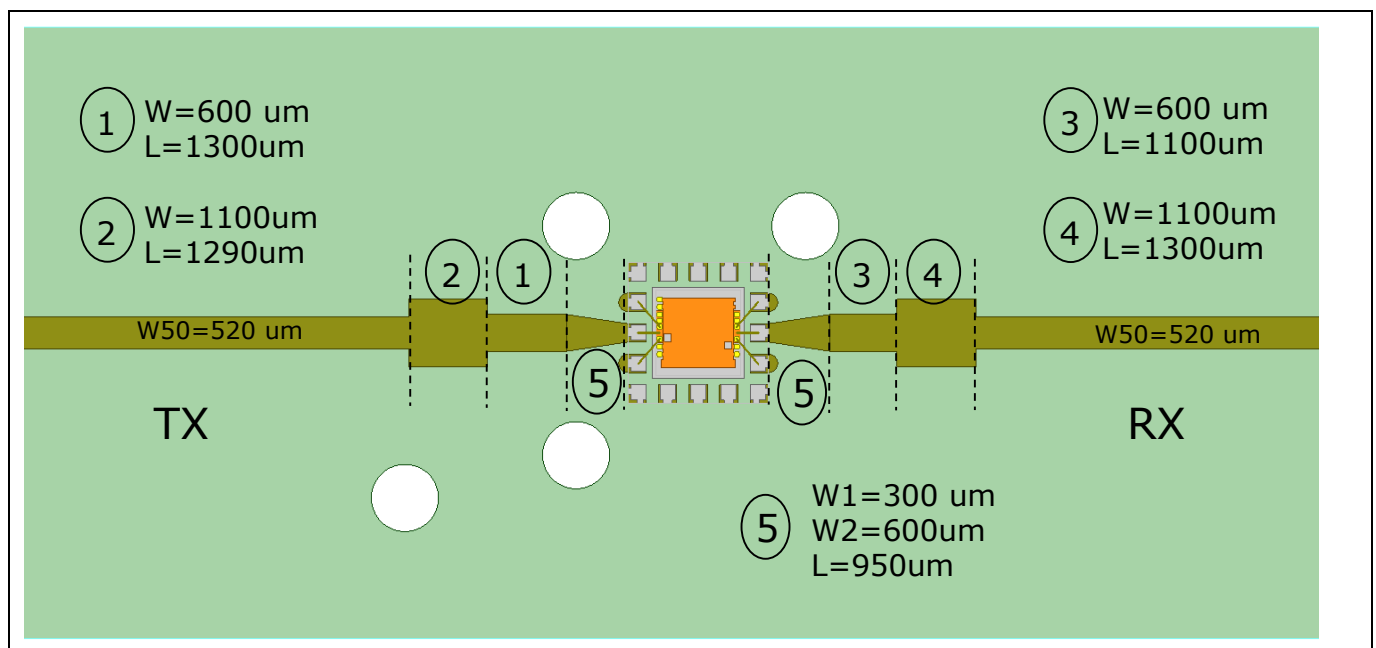


Figure 13 Matching structures to be used on a Ro4350B substrate with a thickness of 0.254 mm

3.2 Layout

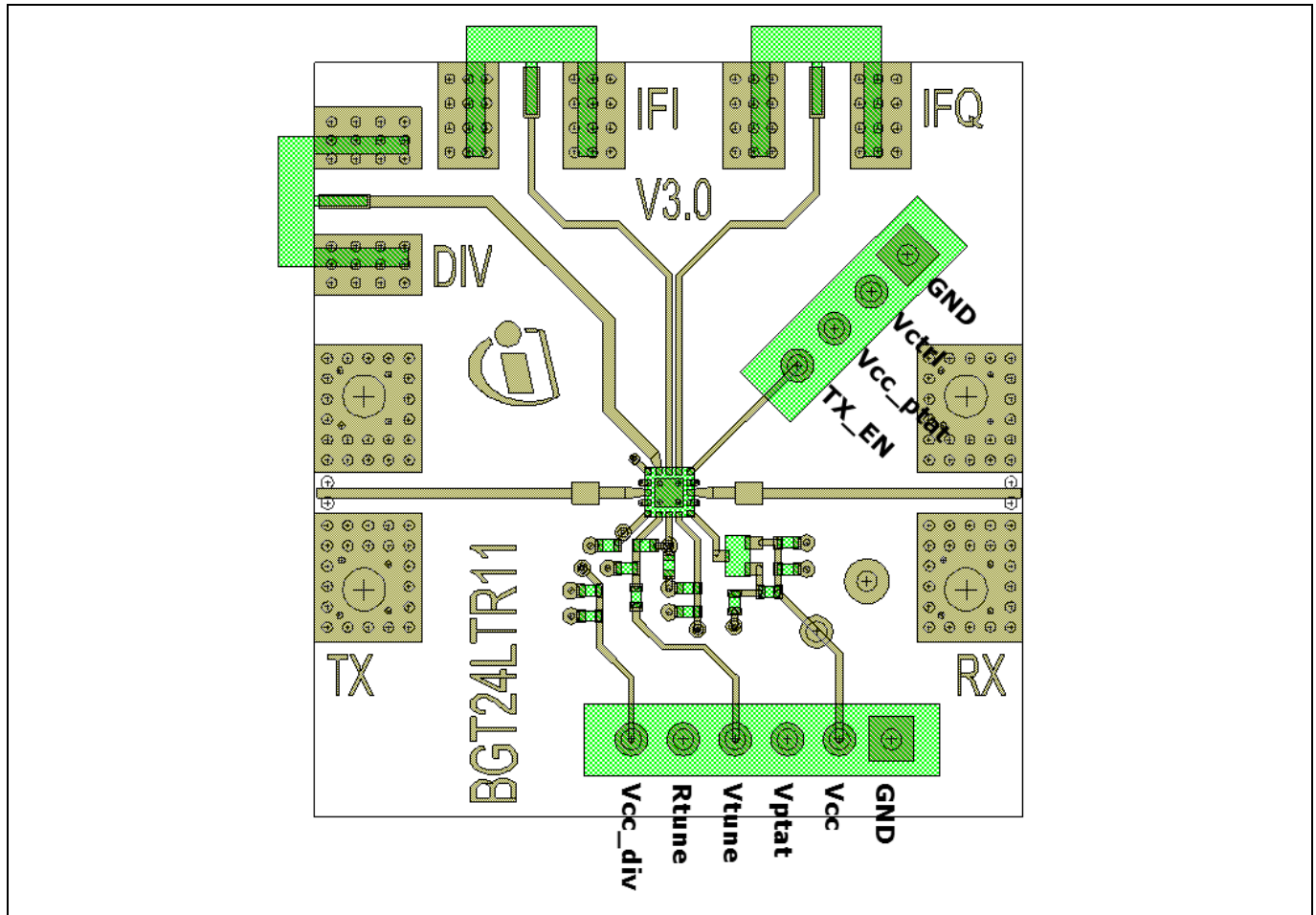


Figure 14 Layout of evaluation board with description of pin headers

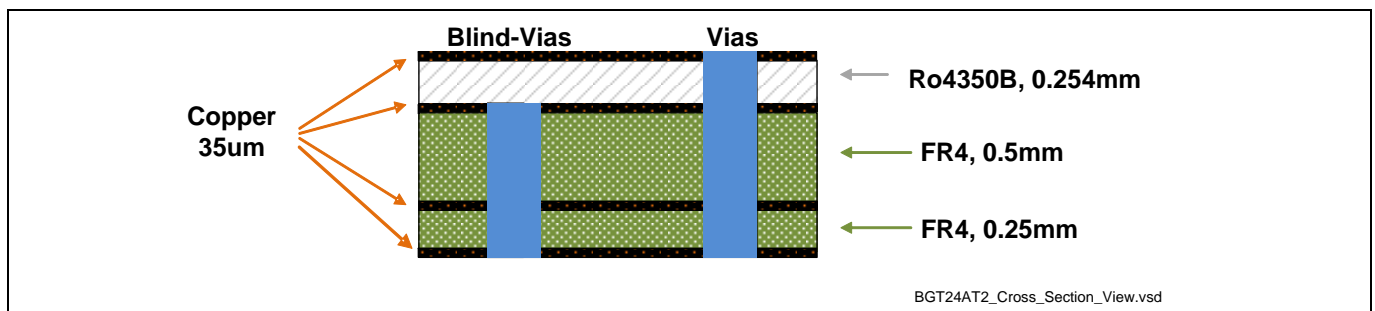


Figure 15 Layer stack

4 Controlling the VCO

4.1 Controlling the VCO using V_PTAT

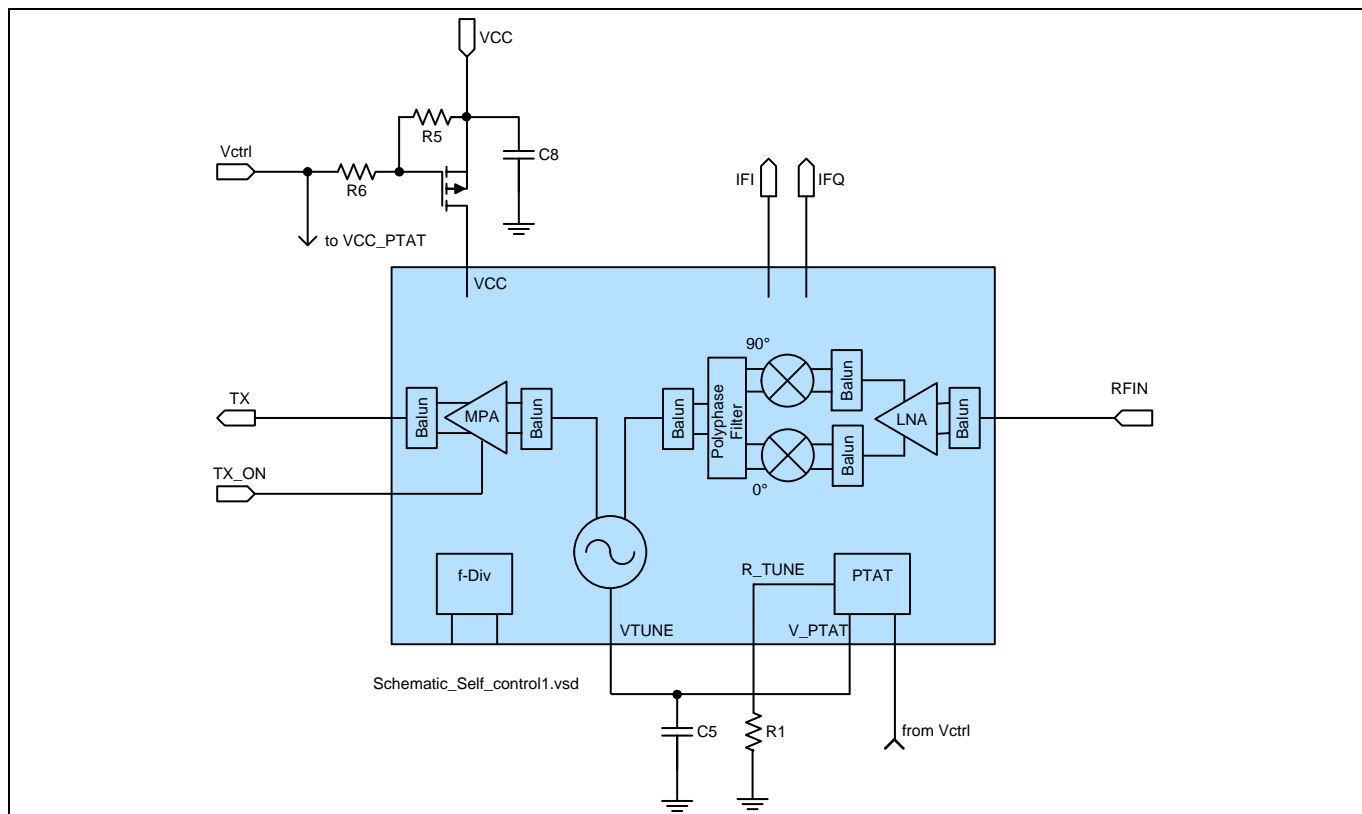


Figure 16 Block diagram: Using V_PTAT to keep BGT24LTR11N16 in the ISM band

Exact frequency control in Doppler radars in the 24 GHz ISM band is not really necessary for most applications. If we assume the transmit frequency to be at the lower edge of the band while it is actually at the upper edge the introduced error is only 0.8 %.

BGT24LTR11N16 was designed to keep its transmit frequency inside the ISM band without the need for a dedicated frequency control circuit like a Phase Locked Loop (PLL) or a look-up table based control of VTUNE.

To achieve this capacitor C5 is charged by V_PTAT while the rest of the chip is turned off to save power. Once C5 is fully charged VCC_PTAT is disconnected while VCC is applied and VTUNE gets its voltage from C5.

There are two reasons for toggling VCC and VCC_PTAT. The first one is obvious: Turning off VCC and VCC_PTAT reduces current consumption (45 mA and 1.5mA, respectively). The second reason for turning off VCC_PTAT is that the PTAT source generates noise at its output when running and this noise on the tuning voltage will degrade the signal to noise ratio (SNR) of the system. Of course for some short range this SNR might still be acceptable.

4.1.1 Controlling the VCO with the PTAT source in detail

One duty-cycle works as follows:

1. TX_ON = 0 V. Disables TX output to prevent out of band emissions.
2. Vctrl = 3.3 V. This turns on the PTAT source (VCC_PTAT = 3.3 V) while VCC is disconnected from power supply.

4.3 Controlling the VCO using a Software Based Open-Loop Concept

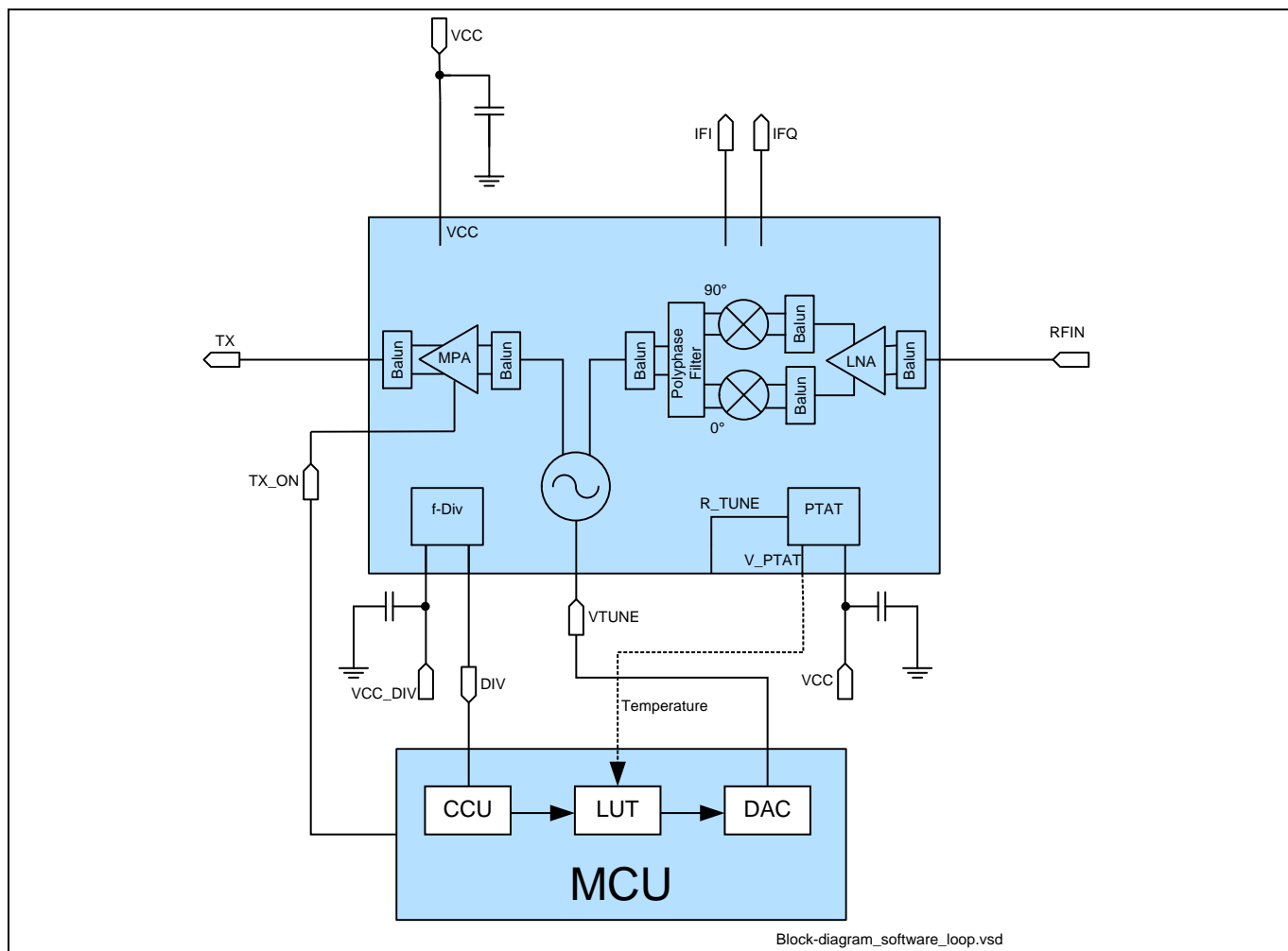


Figure 18 Block diagram: Controlling BGT24LTR11N16 with an Open-Loop concept

It is possible to control BGT24LTR11N16 using an Open-Loop concept, sometimes also called Software-Loop concept. Figure 18 shows a block diagram on how to set-up the system.

- The frequency divider is set to an 8192 division ratio and fed to a Capture Compare Unit (CCU) of the microcontroller to determine the frequency of the oscillator.
- The PTAT source is used as a chip temperature sensor and V_PTAT is fed to an ADC of the microcontroller.
- The microcontroller's DAC is used to generate the tuning voltage of the VCO.
- A GPIO port of the microcontroller enables / disables BGT24LTR11N16's TX output.

Controlling BGT24LTR11N16 with an Open-Loop concept works as follows:

1. Disable TX output
2. Check the chip temperature
3. Generate a Look-Up Table (LUT) that gives the DAC values corresponding to different VCO frequencies. Use this LUT for the modulation of the VCO.
4. Enable TX output
5. Generate transmit signal using DAC
6. Check chip temperature. If chip temperature changed goto 1 else goto 5

5 Authors

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Revision History

Major changes since the last revision

Page or Reference	Description of change

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